

PHOTO TRANSISTOR

General Description

The OST-23G is high sensitivity NPN silicon photo transistor mounted in a black side-looking package , is compact , low profile and easy to mount.



Features

- Compact
- Low profile package
- Low cost plastic package
- With daylight filter
- Meet RoHS

Applications

- Optical sensor
- Photo interrupters

MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
C-E voltage	VCEO	30	V
E-C voltage	VECO	5	V
Collector power dissipation	Pc	100	mW
Operating temp.	Topr.	-45 ~ +85	°C
Storage temp.	Tstg.	-45 ~ +100	°C
Soldering temp. *1	Tsol.	260	°C

*1. For MAX. 5 seconds at the position of 2mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
C-E breakdown voltage	V(BR)CEO	Ic=0.1mA,Ee=0mW/cm ²	30	-	-	V
E-C breakdown voltage	V(BR)ECO	I _R =0.1mA,Ee=0mW/cm ²	5	-	-	V
C-E saturation voltage	VCE(sat)	Ic=0.1mA,Ee=1mW/cm ²	-	-	0.5	V
Switching Speeds	Rise time	tr	Vce=5V,F=100Hz RL=1000Ω	10	-	usec
	Fall time	tf		15	-	usec
Spectral sensitivity	λ		880 ~ 1000			nm
Peak wavelength	λ p		-	940	-	nm
Half angle	Δ θ		-	±20	-	deg.

*2. Illumination is applied by a tungsten lamp of 2856K

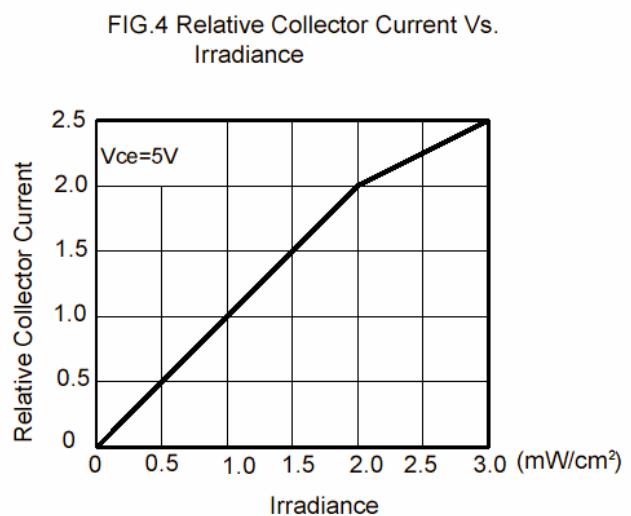
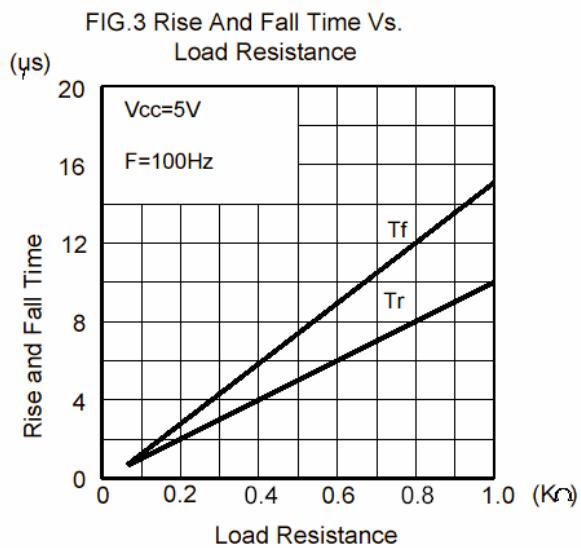
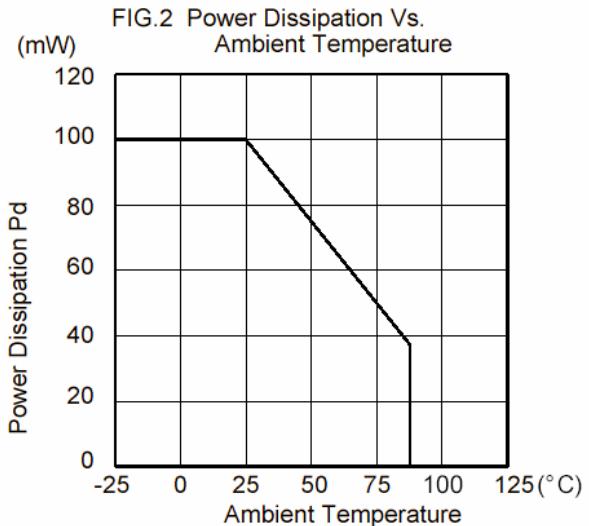
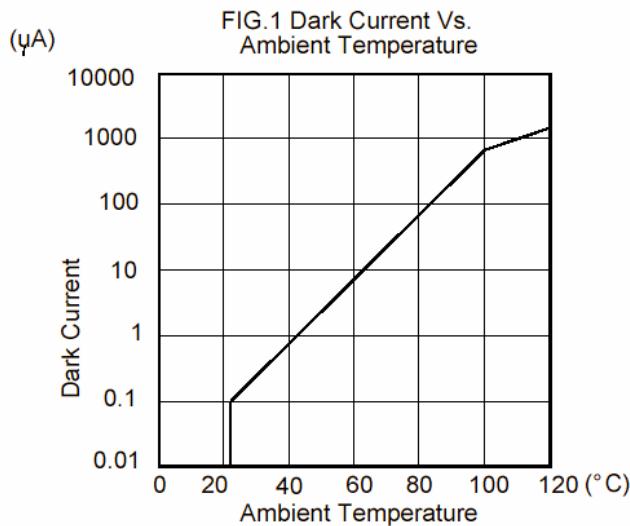


Fig.5 Receive Wavelength

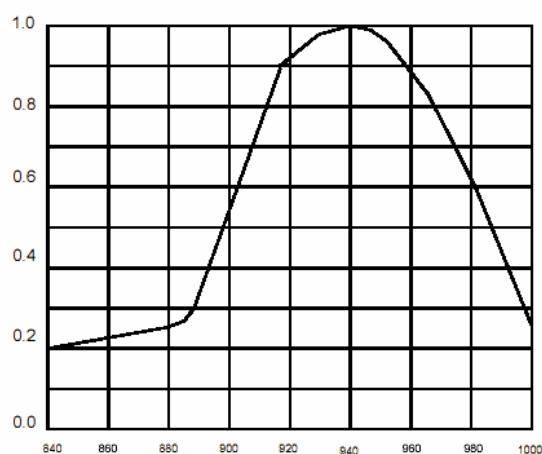
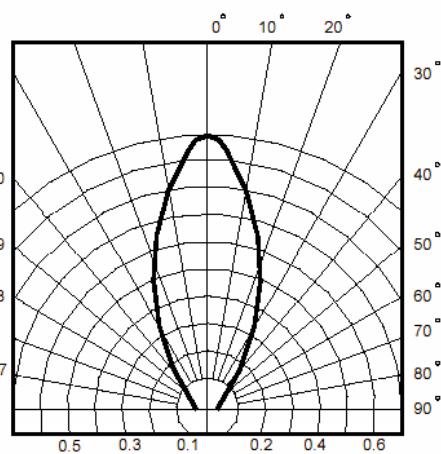
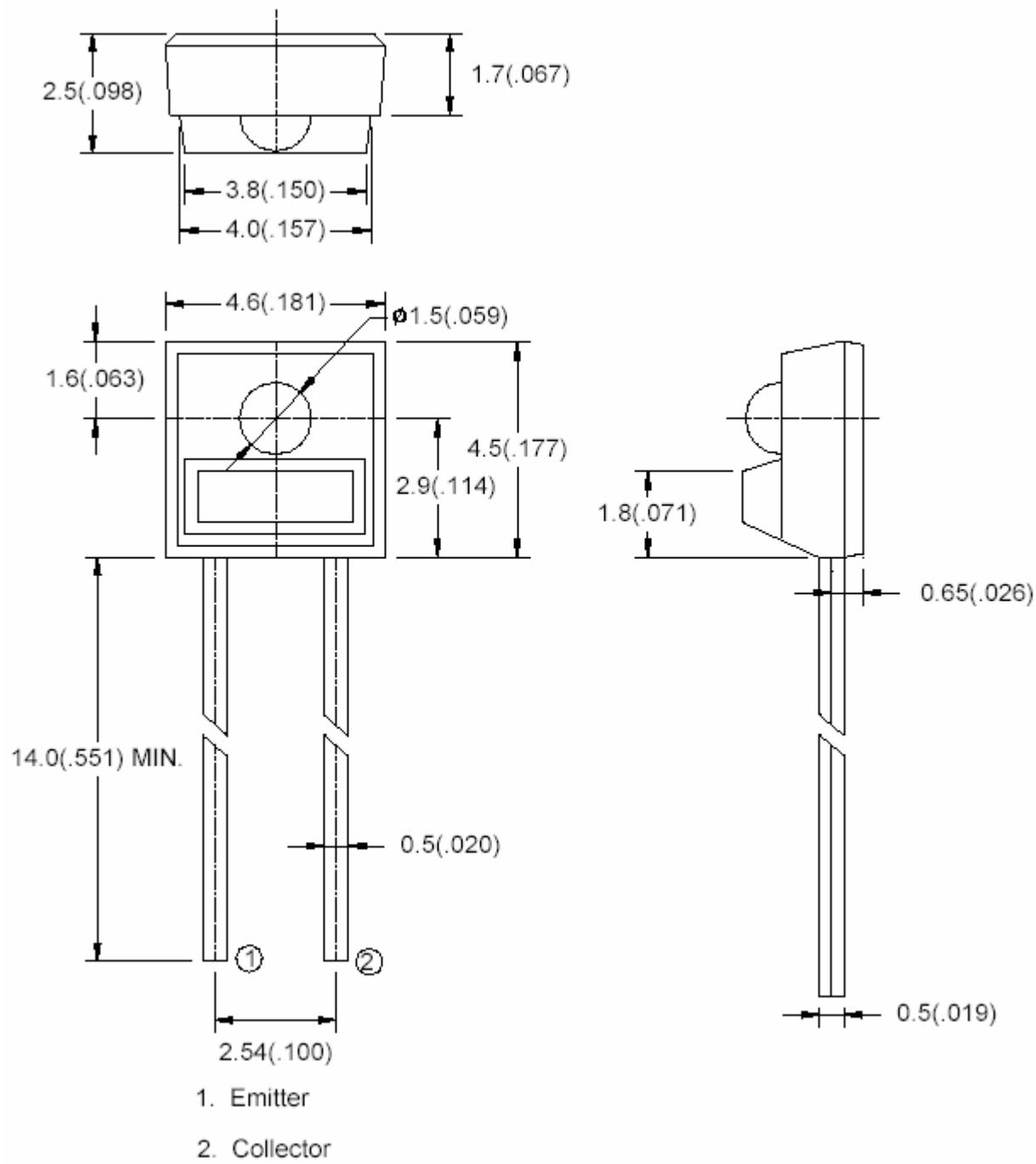


FIG.6 Directivity characteristics



DIMENSIONS



NOTES :

1. All dimensions are in millimeters.
2. Tolerance is $\pm 0.25\text{mm}$ unless otherwise specified.
3. Specifications are subject to change without notice.